

METHOD FOR SHRINKING A DIMENSION OF A GATE

A method for shrinking a dimension of a gate is provided that utilizes a thermal oxidation to form an oxide layer on a semiconductor substrate and a gate. Controlling the thickness of the oxide layer on the gate will control the channel length of a gate. The oxide layer on the gate is stripped by a suitable etching solution and then shrinkage of the dimension of the gate is achieved. That is, an ability of a photolithography is overcome, moreover; shrinking the dimension of the gate to reach an advanced process by the most economical method.